

Amendments to the Specification

Please replace the paragraph beginning on page 6, line 13 with the following amended paragraph:

~~Fig. 4~~ Fig. 1A is a schematic sectional view showing part of the semiconductor device according to the invention.

Please replace the paragraph beginning on page 7, line 21 with the following amended paragraph:

In this way, the configuration shown in ~~Fig. 4~~ Fig. 1B is in just a structure where in the example of the conventional configuration shown in Fig. 4A ~~Fig. 4~~, the Si substrate 200 is omitted, the N⁺ region 202 is replaced with the Si substrate 100, the P⁺ region 204 is replaced with the N⁺ region 102, and the conductive plug 210a is replaced with the PN junction plug portion 108a.

Please replace the paragraph beginning on page 8, line 11 with the following amended paragraph:

Therefore, when the bottom area of the P⁺ polysilicon plug 109 is formed equally to the area of the PN junction 205 on the P⁺ region 204 parallel to the main surface of the Si substrate 200 shown in Fig. 4A, the structure is made to be such a structure that the P⁺ polysilicon plug 109 is formed on such N⁺ region 102, thereby the area of the PN junction is only the area of the bottom 107 of the P⁺ polysilicon plug 109, therefore,

since the area of the PN junction on the sides in the conventional structure is eliminated, the leakage current can be reduced. Moreover, as shown by arrows in Figs. 1A and 1B Fig.4, the charge-up current generated in the plasma treatment such as sputtering or dry etching in the formation of the wiring can be controlled to flow one-way rather than in many directions as in the conventional PN junction.

Please replace the paragraph beginning on page 8, line 25 with the following amended paragraph:

The best mode production method of the semiconductor device for practicing the invention is described with reference to Figs. 2A – 2E and Figs. 3A – 3C Figs.2 and Fig.3.